Notice of Allowability	Application No.	Applicant(s)	
	10/724,687	LEE ET AL.	
	Examiner	Art Unit	
	ANH PHUNG	2824	
The MAILING DATE of this communication apperature All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED or other appropriate comr GHTS. This application is	in this application. If not include nunicationwill be mailed in due	led course. THIS
1. This communication is responsive to			
2. The allowed claim(s) is/are 1-20.			
3. \boxtimes The drawings filed on <u>02 December 2003</u> are accepted by	the Examiner.		
 4. Acknowledgment is made of a claim for foreign priority una) All b) Some* c) None of the: Certified copies of the prioritydocuments have Certified copies of the priority documents have Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE 5. A SUBSTITUTE OATH OR DECLARATION must be submit 	been received. been received in Applica cuments have been received in Applica cuments have been received this communication to facilities.	tion No yed in this national stage application ile a reply complying with the re	equirements
INFORMAL PATENT APPLICATION (PTO-152) which give 6. CORRECTED DRAWINGS (as "replacement sheets") mus	s reason(s) why the oath	or declaration is deficient.	01102 01
(a) ☐ including changes required by the Notice of Draftspers		ew (PTQQ48) attached	
1) hereto or 2) to Paper No./Mail Date .	on a rate it brawing revi	ew (1 19040) attached	
(b) including changes required by the attached Examiner's Paper No./Mail Date	s Amendment / Comment	or in the Office action of	
Identifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in the			e back) of
7. DEPOSIT OF and/or INFORMATION about the depos attached Examiner's comment regarding REQUIREMENT I			ote the
Attachment(s)			
1. Notice of References Cited (PTO-892)	_	nformal Patent Application (PT0	D-152)
2. Notice of Draftperson's Patent Drawing Review (PTO948)	Paper No	Summary (PTO-413), ./Mail Date	
3. Information Disdosure Statements (PTO-1449 or PTO/SB/08 Paper No./Mail Date 2/5/04		s Amendment/Comment	
 Examiner's Comment Regarding Requirement for Deposit of Biological Material 	6. ⊠ Examiner: 9. ⊠ Other <u>Sea</u>	s Statement of Reasons for Allo	warice
		ANH PHUNG	
U.S. Patent and Trademark Office	PR	MARY EXAMINER	

U.S. Patent and Trademark Office PTOL-37 (Rev. 1-04) Application/Control Number: 10/724,687 Page 2

Art Unit: 2824

Detailed Action

1. In response to the U.S. Patent Application Serial No. 10/724,687 filed on December 2, 2003, claims **1-20** are pending in the application.

Priority

2. Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

Information Disclosure Statement

This office acknowledges receipt of the following items from the Applicant:
 Information Disclosure Statement (IDS) filed on February 5, 2004.
 Information disclosed and listed on PTO 1449 was considered.

Examiner's Statement of Reasons for Allowance

4. Claims **1-20** are allowed.

Nii (US 6,590,802), Wong (US 6,341,083) and Hobson (US 5,754,468) disclose a dual port semiconductor memory device similar to that of the present application, but fail to teach:

"wherein the first PMOS transistor and the second PMOS transistor are disposed in the P+-type active region of the N-well area; and the first NMOS transistor, the second NMOS transistor, the third NMOS transistor, the fourth NMOS transistor, the fifth NMOS transistor, and the sixth NMOS transistor are formed in the n+-type active region of the contiguous P-well area" as claim in the independent claim 1; or

"wherein the first PMOS transistor and the second PMOS transistor are disposed in the P+-type active region of the N-well area; and the first NMOS transistor, the

Art Unit: 2824

second NMOS transistor, the third NMOS transistor, the fourth NMOS transistor, and the fifth NMOS transistor are formed in the n+-type active region of the contiguous P-well area" as claim in the independent claim 11.

Any comments considered necessary by applicants must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comment on Statement of Reasons for Allowance".

Conclusion

5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to **ANH PHUNG** whose telephone number is **(571) 272-1883**. The examiner can normally be reached on Monday-Friday from 8:00 AM to 4:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, **RICHARD ELMS**, can be reached on **(571) 272-1869**. The fax phone number for the organization where this application or proceeding is assigned is **(703) 872-9306**.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should

Application/Control Number: 10/724,687

Art Unit: 2824

you have questions on access to the Private PAIR system, contact the Electronic

Business Center (EBC) at 866-217-9197 (toll-free).

Art Unit: 2824

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ANH PHUNG PRIMARY EXAMINER Page 4